



STM9926

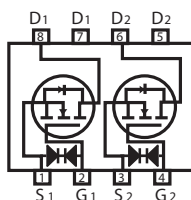
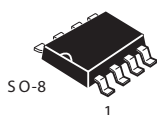
Dual N-Channel Enhancement Mode Field Effect Transistor

PRODUCT SUMMARY

V _{DS}	I _D	R _{DS(ON)} (m Ω) Max
20V	6.5A	28 @ V _{GS} = 4.0V 38 @ V _{GS} = 2.5V

FEATURES

- Super high dense cell design for low R_{DS(ON)}.
- Rugged and reliable.
- Surface Mount Package.
- ESD Protected.



ABSOLUTE MAXIMUM RATINGS (T_A=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	20	V
Gate-Source Voltage	V _{GS}	±10	V
Drain Current-Continuous ^a @ T _J =25°C -Pulsed ^b	I _D	6.5	A
	I _{DM}	30	A
Drain-Source Diode Forward Current ^a	I _S	1.7	A
Maximum Power Dissipation ^a	P _D	2	W
Operating Junction and Storage Temperature Range	T _J , T _{STG}	-55 to 150	°C

THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Ambient ^a	R θ JA	62.5	°C/W
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ELECTRICAL CHARACTERISTICS (T_A=25 °C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ ^c	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250uA	20			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =16V, V _{GS} =0V			1	uA
Gate-Body Leakage	I _{GSS}	V _{GS} = ±10V, V _{DS} =0V			±10	uA
ON CHARACTERISTICS ^b						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D = 250uA	0.5	0.9	1.5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =4.0V, I _D = 6.5A		23	28	m ohm
		V _{GS} =2.5V, I _D = 5A		30	38	m ohm
Forward Transconductance	g _{FS}	V _{DS} = 5.0V, I _D = 6.5A		16		S
DYNAMIC CHARACTERISTICS ^c						
Input Capacitance	C _{ISS}	V _{DS} =8V, V _{GS} = 0V f =1.0MHz		540		pF
Output Capacitance	C _{OSS}			160		pF
Reverse Transfer Capacitance	C _{RSS}			100		pF
SWITCHING CHARACTERISTICS ^c						
Turn-On Delay Time	t _{D(ON)}	V _{DD} = 10V, I _D = 1A, V _{GEN} = 4.5V, R _L = 10 ohm R _{GEN} = 10 ohm		15		ns
Rise Time	t _r			20		ns
Turn-Off Delay Time	t _{D(OFF)}			36		ns
Fall Time	t _f			11		ns
Total Gate Charge	Q _g	V _{DS} =10V, I _D =6.5A, V _{GS} =4V		6.4		nC
		V _{DS} =10V, I _D =6.5A, V _{GS} =2.5V		4.6		nC
Gate-Source Charge	Q _{gs}	V _{DS} =10V, I _D = 6.5 A V _{GS} =4V		1.1		nC
Gate-Drain Charge	Q _{gd}			2.8		nC

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ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ ^c	Max	Unit
DRAIN-SOURCE DIODE CHARACTERISTICS ^b						
Diode Forward Voltage	V _{SD}	V _{GS} = 0V, I _S =1.7A		0.72	1.2	V

Notes

- a.Surface Mounted on FR4 Board, t≤10sec.
- b.Pulse Test:Pulse Width≤ 300us, Duty Cycle≤ 2%.
- c.Guaranteed by design, not subject to production testing.

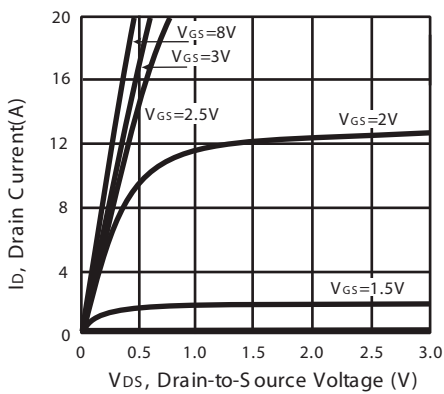


Figure 1. Output Characteristics

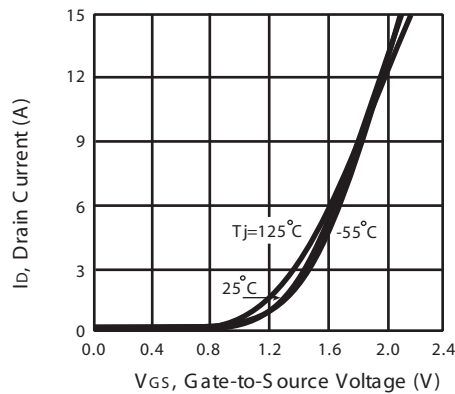


Figure 2. Transfer Characteristics

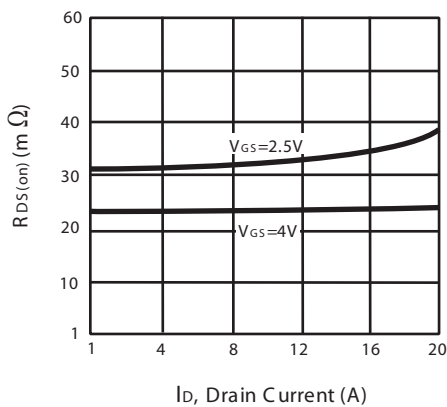


Figure 3. On-Resistance vs. Drain Current and Gate Voltage

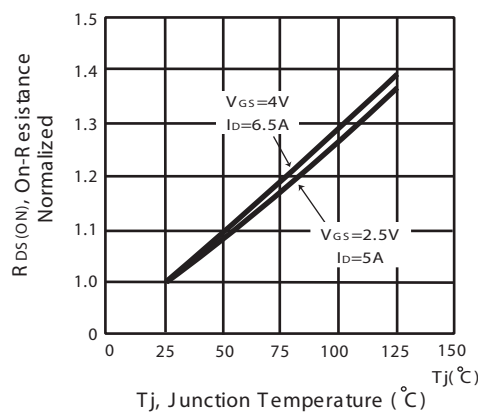


Figure 4. On-Resistance Variation with Drain Current and Temperature

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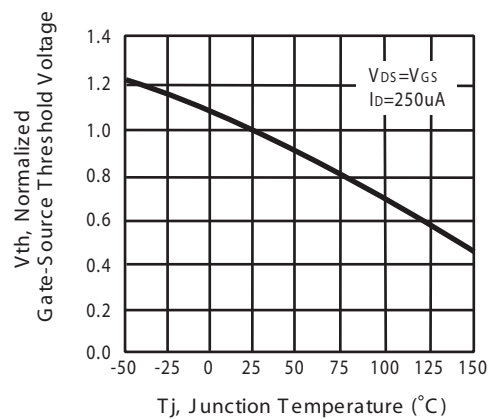


Figure 5. Gate Threshold Variation with Temperature

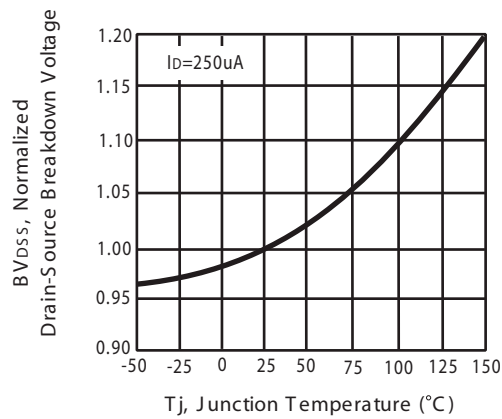


Figure 6. Breakdown Voltage Variation with Temperature

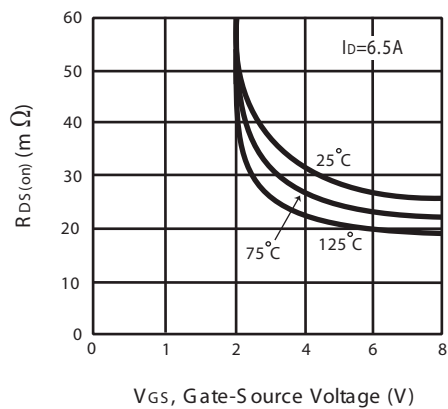


Figure 7. On-Resistance vs. Gate-Source Voltage

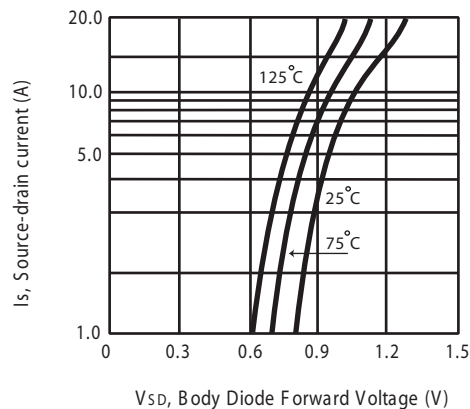


Figure 8. Body Diode Forward Voltage Variation with Source Current

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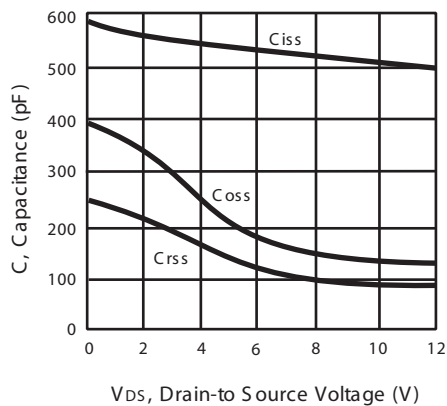


Figure 9. Capacitance

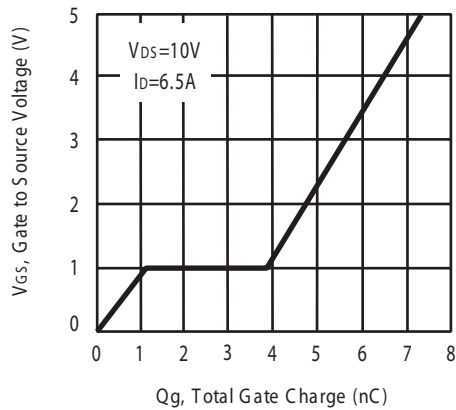


Figure 10. Gate Charge

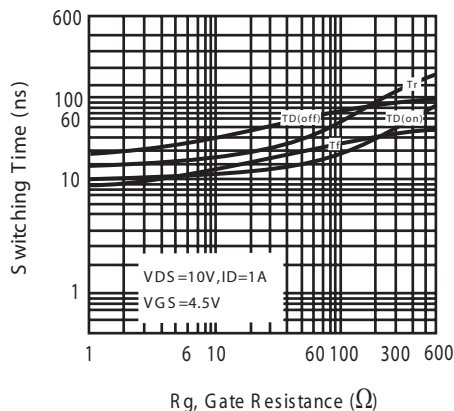


Figure 11. switching characteristics

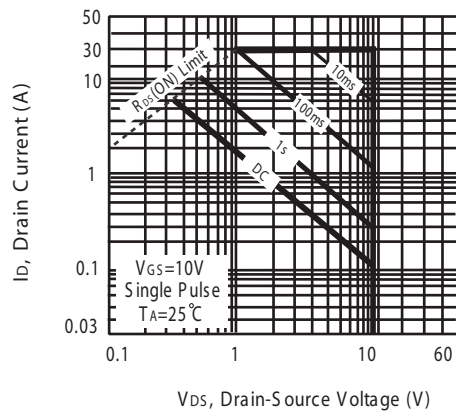
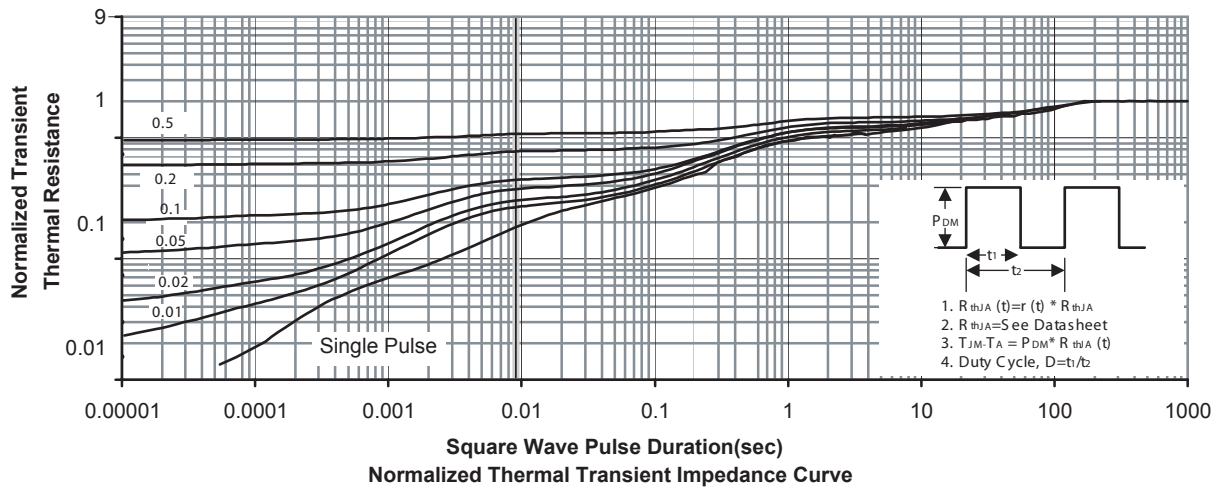


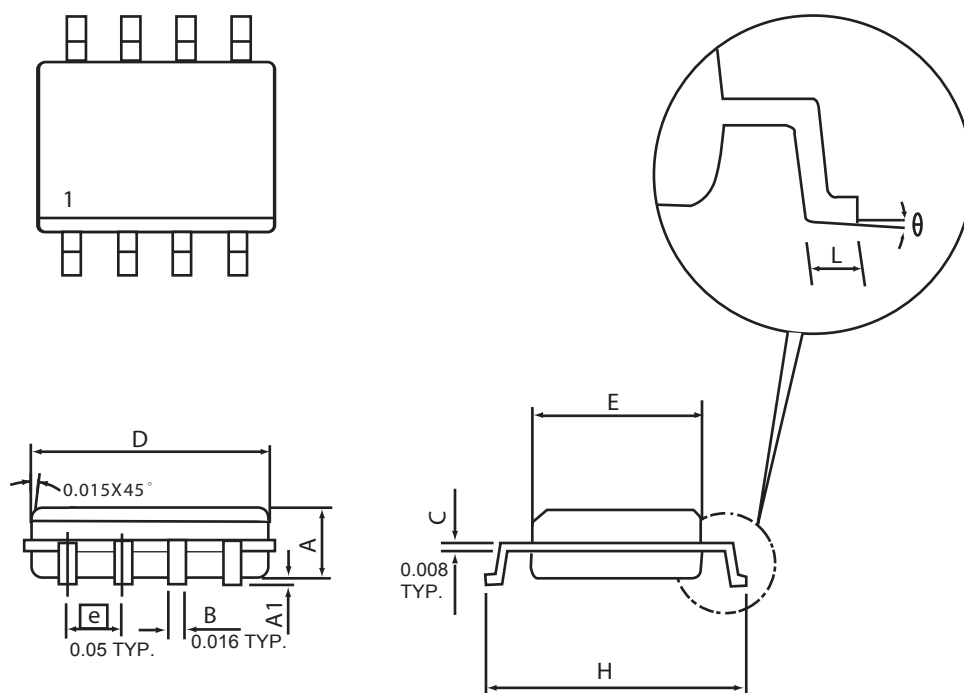
Figure 12. Maximum Safe Operating Area



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PACKAGE OUTLINE DIMENSIONS

SO-8

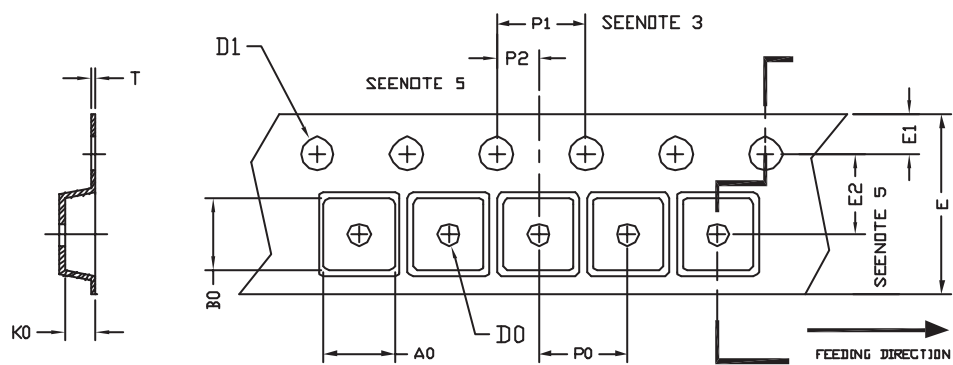


SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	1.35	1.75	0.053	0.069
A1	0.10	0.25	0.004	0.010
D	4.80	4.98	0.189	0.196
E	3.81	3.99	0.150	0.157
H	5.79	6.20	0.228	0.244
L	0.41	1.27	0.016	0.050
θ	0°	8°	0°	8°

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SO-8 Tape and Reel Data

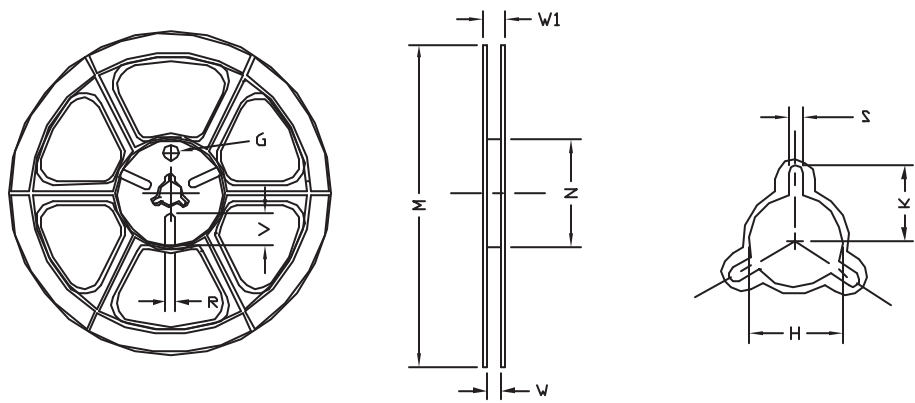
SO-8 Carrier Tape



unit:mm

PACKAGE	A0	B0	K0	D0	D1	E	E1	E2	P0	P1	P2	T
SOP 8N 150mil	6.40	5.20	2.10	$\phi 1.5$ (MIN)	$\phi 1.5$ + 0.1 - 0.0	12.0 ± 0.3	1.75	5.5 ± 0.05	8.0	4.0	2.0 ± 0.05	0.3 ± 0.05

SO-8 Reel



UNIT:mm

TAPE SIZE	REEL SIZE	M	N	W	W1	H	K	S	G	R	V
12 mm	$\phi 330$	330 ± 1	62 ± 1.5	12.4 + 0.2	16.8 - 0.4	$\phi 12.75$ + 0.15	---	2.0 ± 0.15	---	---	---